

## Description

μPD71082 and μPD71083 are CMOS 8-bit transparent latches with three-state output buffers. They are used as bus buffers or bus multiplexers in microprocessor systems. Their high-drive capability makes them suitable for data latch, buffer, or I/O port applications.

## Features

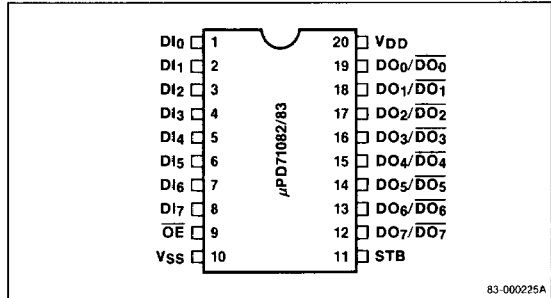
- CMOS technology
- 8-bit parallel data register
- Three-state output buffer
- High drive capability output buffer ( $I_{OL} = 12 \text{ mA}$ )
- μPD8085A, 8048, 8086, 8088, μPD70108/116, and μPD70208/216 system compatible
- μPD71082 — non-inverted output;  
μPD71083 — inverted output
- Single +5 V ±10% power supply
- Transparent operation
- Industrial temperature range: -40 to +85°C

## Ordering Information

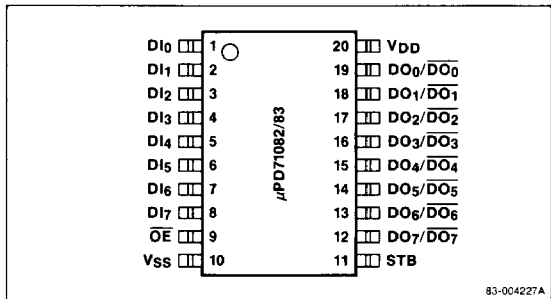
Part Number	Package	Output
μPD71082C	20-pin plastic DIP	Non-inverted
μPD71082G	20-pin plastic SOP	
μPD71083C	20-pin plastic DIP	Inverted
μPD71083G	20-pin plastic SOP	

## Pin Configurations

### 20-Pin Plastic DIP



### 20-Pin Plastic SOP



5h

## Pin Identification

Symbol	Function
DI <sub>0</sub> -DI <sub>7</sub>	Data input, bits 0-7
DO <sub>0</sub> -DO <sub>7</sub> / DO <sub>0</sub> -DO <sub>7</sub>	Data output, bits 0-7; non-inverted (μPD71082) or inverted (μPD71083)
STB	Strobe input
OE	Output enable input
V <sub>DD</sub>	+5 V power supply
V <sub>SS</sub>	Ground

### PIN FUNCTIONS

#### DI<sub>0</sub>-DI<sub>7</sub> (Data Input)

DI<sub>0</sub>-DI<sub>7</sub> are data input lines to the 8-bit data latch. Data on DI lines passes through the latch while STB is high. The data is latched to DO/DO with the falling edge of STB.

#### DO<sub>0</sub>-DO<sub>7</sub>/DO<sub>0</sub>-DO<sub>7</sub> (Data Output)

DO<sub>0</sub>-DO<sub>7</sub>/DO<sub>0</sub>-DO<sub>7</sub> are the three-state data output lines from the 8-bit data latch. When OE is high, these lines go into the high-impedance state. When OE is low, data from the latch is output, either non-inverted (μPD71082) or inverted (μPD71083).

#### STB (Strobe)

STB is the input strobe signal for the 8-bit latch. When STB is high, data on the DI lines passes through the 8-bit

latch. Data is latched on the falling edge of STB. When STB is low, the DO<sub>0</sub>-DO<sub>7</sub>/DO<sub>0</sub>-DO<sub>7</sub> outputs do not change.

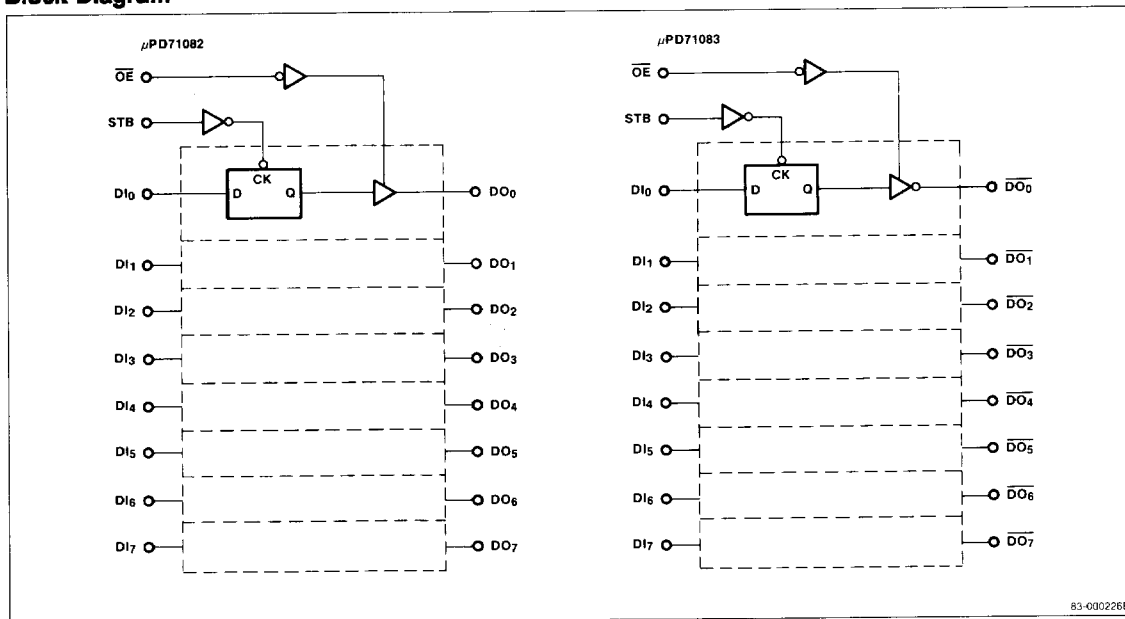
#### OE (Output Enable)

OE input is the output enable signal for the three-state DO/DO lines. When OE is high, DO/DO lines are high impedance. When OE is low, data from the 8-bit latch is output to DO<sub>0</sub>-DO<sub>7</sub>/DO<sub>0</sub>-DO<sub>7</sub>. See table 1.

**Table 1. Latch Operation**

STB	OE	DO <sub>0</sub> -DO <sub>7</sub> /DO <sub>0</sub> -DO <sub>7</sub>	8-Bit Data Latch
Low	Low	Latched data from 8-bit data latch is enabled	DI line data has been latched with falling edge of STB (high to low)
	High	High impedance	
High	Low	Data on DI <sub>0</sub> -DI <sub>7</sub>	DI passed through to DO/DO
	High	High Impedance	

### Block Diagram



### FUNCTIONAL DESCRIPTION

The μPD71082 and μPD71083 are 8-bit data latches strobed by the STB signal. They have high-drive capability output buffers controlled by the  $\overline{OE}$  signal. Data on the DI lines is latched by the trailing edge of STB (high to low). When STB is high, data passes through the latch. When  $\overline{OE}$  is high, DO lines are high impedance. When  $\overline{OE}$  is low, the contents of the latches are output on  $DO_0$ - $DO_7$ . The DO lines are isolated from  $\overline{OE}$  switching noise.

### ELECTRICAL SPECIFICATIONS

#### Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$ ;  $V_{SS} = 0\text{ V}$

Power supply voltage, $V_{DD}$	-0.5 to +7.0 V
Input voltage, $V_I$	-1.0 to $V_{DD} + 1\text{ V}$
Output voltage, $V_O$	-0.5 to $V_{DD} + 0.5\text{ V}$
Power dissipation, $P_{D\text{MAX}}$ , DIP	500 mW
Power dissipation, $P_{D\text{MAX}}$ , SO	200 mW
Operating temperature, $T_{\text{opt}}$	-40 to +85°C
Storage temperature, $T_{\text{stg}}$	-65 to +150°C

Exposing the device to stresses above those listed in the absolute maximum ratings could cause permanent damage. Exposure to absolute maximum ratings for extended periods may affect device reliability.

#### DC Characteristics

$T_A = -40$  to +85°C;  $V_{DD} = 5\text{ V} \pm 10\%$

Parameter	Symbol	Min	Max	Units	Conditions
Input voltage, high	$V_{IH}$	2.2		V	$V_{OL} = 0.45\text{ V}$ $V_{OH} = V_{DD} - 0.8\text{ V}$
Input voltage, low	$V_{IL}$		0.8	V	$V_{OL} = 0.45\text{ V}$ $V_{OH} = V_{DD} - 0.8\text{ V}$
Output voltage, high	$V_{OH}$	$V_{DD} - 0.8$		V	$I_{OH} = -4\text{ mA}$
Output voltage, low	$V_{OL}$		0.45	V	$I_{OL} = 12\text{ mA}$
Input current	$I_I$	-1.0	1.0	μA	$V_I = V_{DD}, V_{SS}$
Leakage current, high impedance	$I_{\text{OFF}}$	-10	10	μA	$\overline{OE} = V_{DD}$
Power supply current (static)	$I_{DD}$		80	μA	$V_I = V_{DD}, V_{SS}$
Power supply current (dynamic)	$I_{DD\text{dyn}}$		20	mA	$f_{\text{in}} = 10\text{ MHz}$ $C = 200\text{ pF}$

#### Capacitance

$T_A = 25^\circ\text{C}$ ;  $V_{DD} = +5\text{ V}$

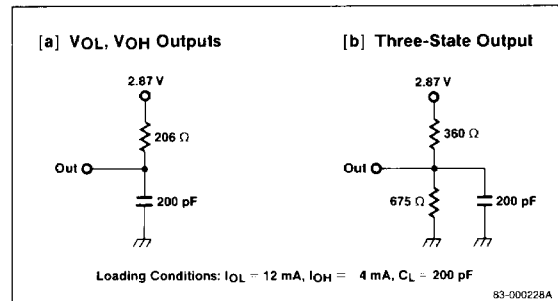
Parameter	Symbol	Min	Max	Units	Conditions
Input capacitance	$C_{\text{in}}$		12	pF	$f = 1\text{ MHz}$

#### AC Characteristics

$T_A = -40$  to +85°C;  $V_{DD} = 5\text{ V} \pm 10\%$

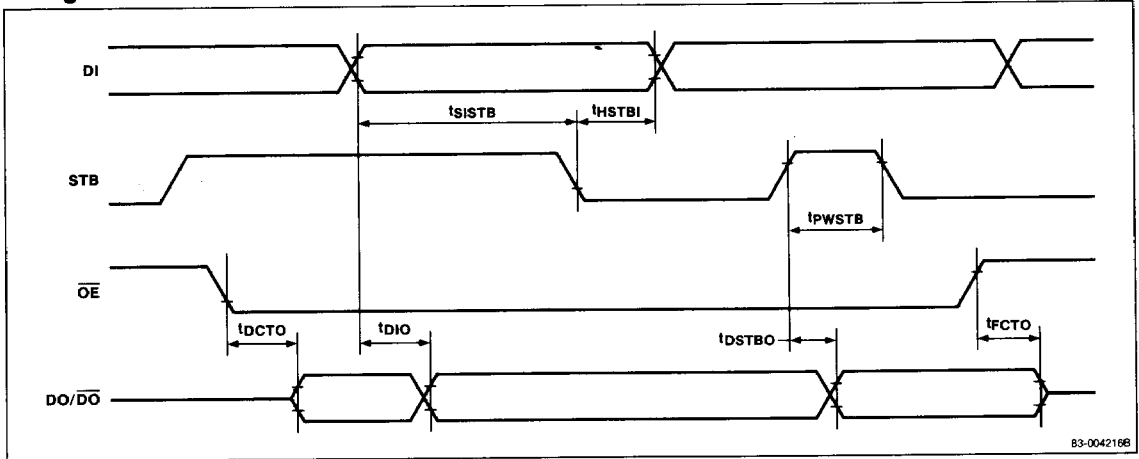
Parameter	Symbol	Min	Max	Units	Conditions
Input to output delay	$t_{DIO}$	5	40	ns	Loading circuit (a)
STB to output delay	$t_{\text{DSTB0}}$	10	60	ns	
Data float time from $\overline{OE}$ high	$t_{\text{FCT0}}$	5	30	ns	Loading circuit (b)
Data output delay from $\overline{OE}$ low	$t_{\text{DCT0}}$	10	40	ns	
Input to STB setup time	$t_{\text{SISTB}}$	0		ns	Loading circuit (a)
Input to STB hold time	$t_{\text{HSTBI}}$	25		ns	
STB high pulse width	$t_{\text{PWSTB}}$	20		ns	
Signal rise time	$t_{\text{LH}}$		20	ns	0.8 to 2.0 V
Signal fall time	$t_{\text{HL}}$		12	ns	2.0 to 0.8 V

#### Loading Circuits for AC Testing



5h

**Timing Waveforms**



**Timing Measurement Points**

